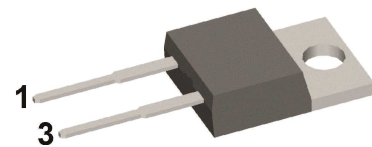


**Features / Advantages:**

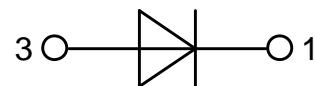
- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)



TO-220-2

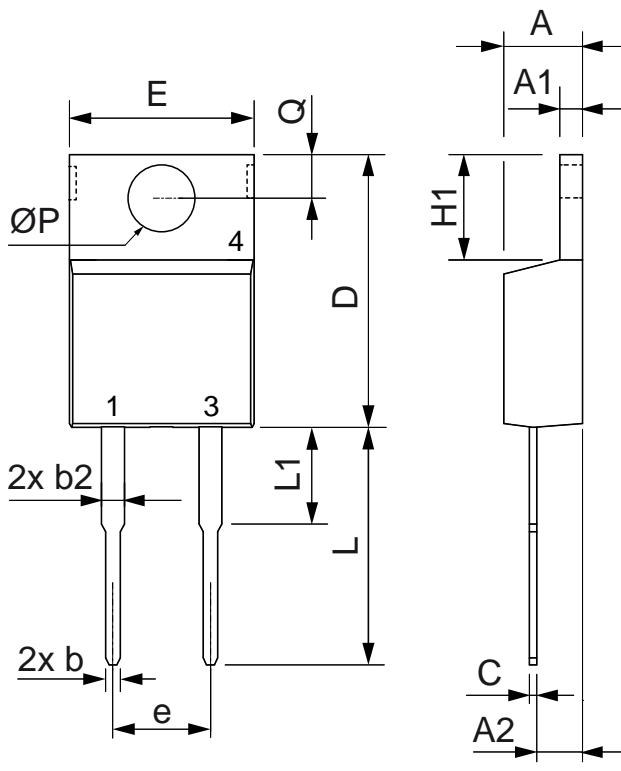


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		600	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		600	V
$I_R$	reverse current, drain current	$V_R = 600 V$		$T_{VJ} = 25^{\circ}C$		100	$\mu A$
		$V_R = 600 V$		$T_{VJ} = 150^{\circ}C$		0.5	mA
$V_F$	forward voltage drop	$I_F = 15 A$		$T_{VJ} = 25^{\circ}C$		2.04	V
						2.25	V
		$I_F = 30 A$		$T_{VJ} = 150^{\circ}C$		1.35	V
						1.59	V
$I_{FAV}$	average forward current	$T_C = 140^{\circ}C$ rectangular	$d = 0.5$	$T_{VJ} = 175^{\circ}C$		15	A
$V_{F0}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}C$		0.99	V
$r_F$	slope resistance					15	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					1.6	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.50		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}C$		95	W
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$		$T_{VJ} = 45^{\circ}C$		110	A
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 MHz$		$T_{VJ} = 25^{\circ}C$		12	pF
$I_{RM}$	max. reverse recovery current	} $I_F = 15 A; V_R = 300 V$		$T_{VJ} = 25^{\circ}C$		5	A
				$T_{VJ} = 100^{\circ}C$		7	A
$t_{rr}$	reverse recovery time	} $-di_F / dt = 200 A/\mu s$		$T_{VJ} = 25^{\circ}C$		35	ns
				$T_{VJ} = 100^{\circ}C$		95	ns



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	<i>RMS current</i>	per terminal			35	A
$T_{VJ}$	<i>virtual junction temperature</i>		-55		175	°C
$T_{op}$	<i>operation temperature</i>		-55		150	°C
$T_{stg}$	<i>storage temperature</i>		-55		150	°C
<b>Weight</b>				2		g
$M_D$	<i>mounting torque</i>		0.4		0.6	Nm
$F_C$	<i>mounting force with clip</i>		20		60	N

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
$\varnothing P$	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125

Fast Diode

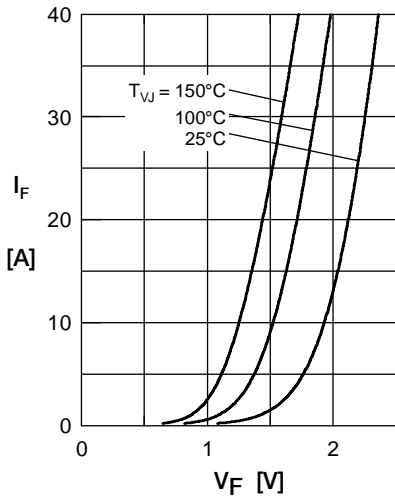


Fig. 1 Forward current  $I_F$  versus  $V_F$

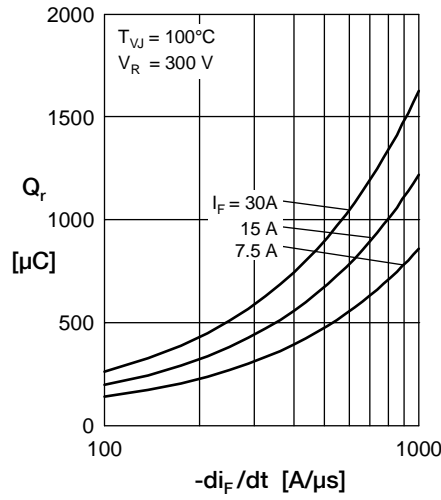


Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$

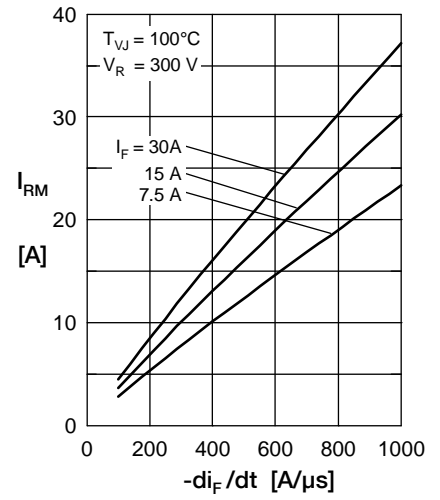


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

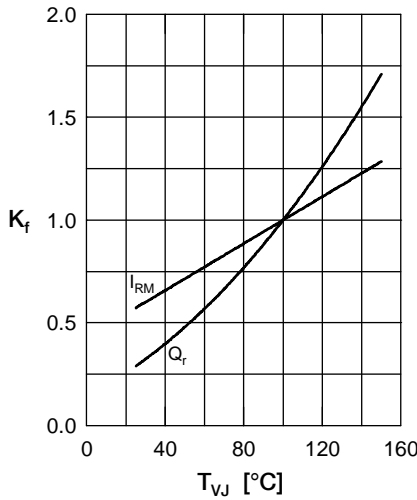


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

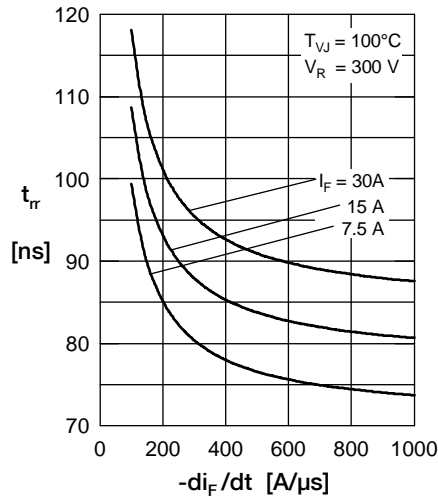


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

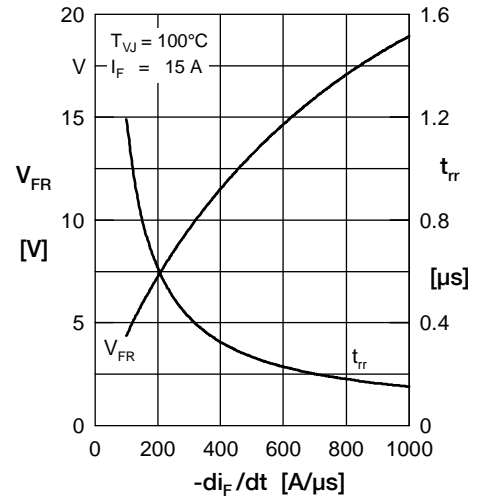


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{rr}$  versus  $di_F/dt$

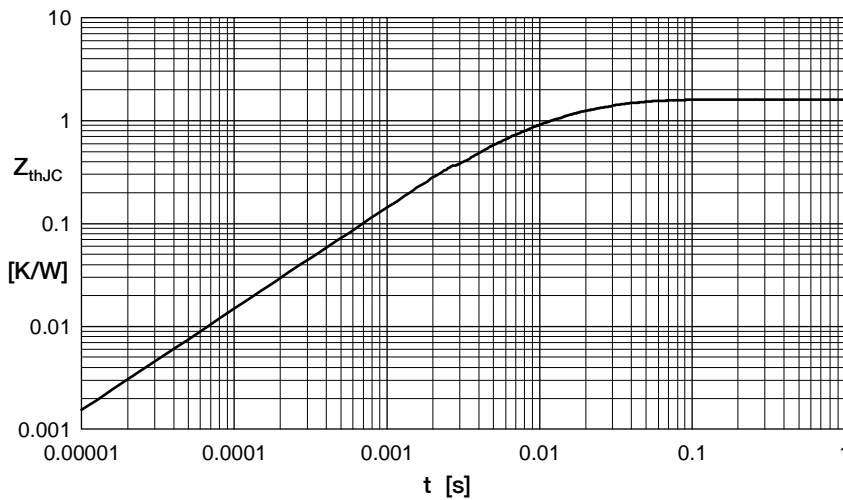


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.908	0.0052
2	0.350	0.0003
3	0.342	0.017